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BURNER FOR FABRICATING AEROSOL DOPED WAVEGUIDES

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FIELD OF THE INVENTION

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This invention relates to a burner for fabricating aerosol doped waveguides. In particular, the invention relates to a modified burner which enables the in-situ delivery of dopant ions in a single step process to an optical waveguide during the deposition stage of fabrication.

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BACKGROUND OF THE INVENTION

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The fabrication of silica based planar waveguides with high ion content by chemical vapour deposition (CVD), and in particular flame hydrolysis deposition (FHD) methods, is already known in the art.

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In such fabrication methods it is often desired to introduce dopant ions during the deposition process. The introduction of dopant ions is effected by a number of known methods which suffer to a greater or lesser degree from certain disadvantages. For example, solution doping requires the core which makes up the waveguide to be partially fused and this introduces

1 several complications.

2

3 An alternative method is to use aerosol doping. In  
4 aerosol doping droplets of an aqueous solution of the  
5 dopant ions are transferred to a modified FHD burner.  
6 The water is evaporated to leave submicron dopant ion  
7 particles. The dopant ions are then oxidised in the  
8 burner flame and can be distributed during the  
9 deposition stage of fabricating the waveguide.

10

11 It is known to modify conventional FHD burners to  
12 incorporate an extra port for the aerosol feed. A  
13 problem arises, however, when such burners are used in  
14 the fabrication of heavily doped waveguides. High  
15 dopant ion levels require high concentrations of the  
16 aqueous dopant ion solution. During the evaporation of  
17 the solvent in highly concentrated solutions, more  
18 dopant ions condense around the aerosol inlet port than  
19 would do with a less concentrated solution. This build  
20 up of condensed ions can create blockages. The present  
21 invention seeks to provide a modified burner design  
22 which obviates or mitigates the problems heretofore  
23 mentioned.

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25 SUMMARY OF THE INVENTION

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27 In accordance with the present invention there is  
28 provided a burner for fabricating aerosol doped  
29 waveguides, the burner including:

30 a plurality of inlet ports each connected to a  
31 respective torch conduit, said torch conduit connecting  
32 its respective inlet port to a gas mixing region; and  
33 including a gas expansion chamber provided for at least  
34 one of said inlet ports upstream of said gas mixing  
35 region.

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1 Preferably, the gas expansion chamber is in the form of  
2 a reservoir chamber.

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4 Preferably, the gas expansion chamber is located at the  
5 junction of an inlet port and the respective torch  
6 conduit.

7

8 Alternatively, the gas expansion chamber is located  
9 upstream of the junction between the inlet port and the  
10 respective torch conduit.

11

12 Alternatively, the gas expansion chamber is located  
13 downstream of the junction of an inlet port and the  
14 respective torch conduit.

15

16 Preferably, said inlet ports feed oxygen, hydrogen,  
17 waveguide deposition material carried by a carrier gas,  
18 and aerosol droplets of a dopant ion solution carried  
19 by a carrier gas to the said burner.

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21 Preferably, the hydrogen port is located downstream of  
22 the waveguide deposition material inlet port.

23

24 Preferably, the aerosol inlet port is located  
25 downstream of the hydrogen inlet port.

26

27 Preferably, the oxygen inlet port is located downstream  
28 of the aerosol inlet port.

29

30 Preferably, said at least one inlet port is located in  
31 a radial plane with respect to a longitudinal axis of  
32 the burner which differs from a radial plane containing  
33 said other inlet ports.

34

35 Preferably, said at least one inlet port is located in  
36 a plane orientated at  $180^\circ$  to the radial plane of the

1 other inlet ports.

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3 Preferably, said at least one inlet port is orientated  
4 at a first angle with respect to the burner axis, and  
5 wherein the other inlet ports are orientated at a  
6 second angle with respect to the burner axis, said  
7 first angle being less than said second angle.

8

9 Preferably, said first angle lies in the range 5° to  
10 45°.

11

12 Preferably, said first angle lies in the range 5° to  
13 25°.

14

15 Preferably, said at least one inlet port is an aerosol  
16 inlet port for providing aerosol droplets of a dopant  
17 ion solution to said burner.

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19 DESCRIPTION OF THE DRAWINGS

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21 Embodiments of the present invention will now be  
22 described by way of example only, with reference to the  
23 drawings in which:

24

25 Fig. 1 is an FHD burner already known in the prior art;

26

27 Fig. 2 is a cross-section through an FHD burner of the  
28 type shown in Fig. 1; and

29

30 Fig. 3 is a cross-section through a modified FHD burner  
31 according to the present invention.

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33 DETAILED DESCRIPTION OF THE INVENTION

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35 Referring to the drawings, Fig. 1 illustrates a FHD  
36 burner 1 already known in the art. The burner 1 has

1 four feed inlet ports: a halide inlet port 2, a  
2 hydrogen inlet port 3, an aerosol inlet port 4, and an  
3 oxygen inlet port 5. The halide inlet port 2 feeds the  
4 burner 1 with halide deposition materials, for example,  
5  $\text{SiCl}_3$ ,  $\text{PCl}_3$ , etc carried by a suitable carrier gas, for  
6 example,  $\text{N}_2$ . The inlet ports 2, 3, 4 and 5 communicate  
7 with a gas mixing region 8 at the output of the burner  
8 1.

9

The aerosol inlet port 4 supplies aerosol droplets of a dopant ion solution, for example, 0.2 M aqueous  $\text{ErCl}_3$ . An atomizer 6 is used to generate the aerosol droplets of the dopant ion solution. The aerosol droplets are carried by a carrier gas, for example,  $\text{N}_2$ , to the aerosol inlet port 4 of the burner 1. The water solvent is then evaporated to leave submicron particles of the dopant ions (here  $\text{Er}^{+3}$ ) which are prone to condense at the inlet port 4. For solution strengths above 0.2M, the build up of condensed dopant ions can create a blockage 7 which can clog the inlet port 4. This blockage 7 occurs before the dopant ions react in the gas mixing reaction zone 8, which affects the rate at which the dopant ions are incorporated during fabrication of a waveguide 9. The blockage 7 arises due to the combination of an abrupt reduction in pipe volume and the change in directionality of the carrier gas flow ( $\theta = 68^\circ$  from the torch axis (X in Fig. 1)).

20

Referring now to Fig. 2, there is shown a cross-section through this type of conventional burner 1. The inlet ports 2, 3, 4 and 5 are all aligned at the same angle  $\theta$  to the torch axis X, and transfer the feed gases (the gas carrying the halide deposition materials, hydrogen, the gas carrying the dopant ions, and oxygen) into concentric torch conduits 10, 11, 12 and 13 respectively. The halide torch conduit 10, hydrogen

1 torch conduit 11, aerosol torch conduit 12, and oxygen  
2 torch conduit 13 deliver the feed gases to the gas  
3 mixing reaction zone 8 located in the burner nozzle 14  
4 where the dopant ions are oxidised in the burner flame.  
5 The oxidised dopant ions are then incorporated during  
6 the deposition of the layers (not shown) which form the  
7 waveguide 9 (shown in Fig.1) a single step process.

8

9 Referring now to Fig. 3, there is shown a modified  
10 burner 15 made in accordance with the invention for  
11 introducing rare earth dopant ions, for example,  $\text{Er}^{+3}$ ,  
12 during fabrication of a waveguide (not shown).

13

14 The burner 15 has four feed inlet ports: a halide inlet  
15 port 16, a hydrogen inlet port 17, an aerosol inlet  
16 port 18, and an oxygen inlet port 19. The halide inlet  
17 port 16 supplies the deposition materials, for example,  
18  $\text{SiCl}_3$ ,  $\text{PCl}_3$ , etc, which are carried by a suitable  
19 carrier gas, for example,  $\text{N}_2$ . The aerosol inlet port 18  
20 supplies aerosol droplets of a dopant ion solution, for  
21 example, aqueous  $\text{ErCl}_3$ .

22

23 The halide inlet port 16, hydrogen port 17, and oxygen  
24 port 19 are located in the same radial plane radiating  
25 from the torch axis Y and can be all aligned at the  
26 same angle  $\theta_1$  to the torch axis Y. The aerosol inlet  
27 port 18 is located in a different radial plane (for  
28 example, it may be displaced by  $180^\circ$  from the plane in  
29 which the inlet ports 16, 17 and 19 are located) and is  
30 positioned at a different angle  $\theta_2$  with respect to the  
31 torch axis Y. The inlet ports 16, 17, 18 and 19  
32 transfer the feed gases into respective concentric  
33 torch conduits 20, 21, 22 and 23. The halide torch  
34 conduit 20, hydrogen torch conduit 21, aerosol torch  
35 conduit 22, and oxygen torch conduit 23 deliver their  
36 respective feed gases to a gas mixing reaction zone 24

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1 where the dopant ions, in this example  $\text{Er}^{+3}$ , are  
2 oxidised in the burner flame (not shown).  
3

4 The aerosol inlet port 18 has a modified structure,  
5 compared to the aerosol inlet port 4 of prior art  
6 burner 1. The aerosol conduit 22 is expanded at the  
7 region where it connects with aerosol inlet port 18 to  
8 form a gas expansion chamber 25 (here in the form of a  
9 reservoir chamber). The gas expansion chamber 25  
10 provides an increase in the volume of the aerosol inlet  
11 port 18 and helps to maintain the concentration of  
12 dopant ions and to mitigate the build up of condensed  
13 dopant ions during evaporation of the aqueous dopant  
14 ion solution.  
15

16 The gas expansion chamber 25 enables the evaporation of  
17 the dopant ion solvent to occur without the dopant ions  
18 condensing at the base of the aerosol inlet port 18  
19 forming a blockage at the base of the aerosol inlet  
20 port 18.

21  
22 A suitable volume for the gas expansion chamber lies in  
23 the range of 2500  $\text{mm}^3$  to 5000  $\text{mm}^3$  for an aerosol feed  
24 carrier gas flow rate of 3 litres/min, an aerosol inlet  
25 port 18 internal diameter of 5.5 mm, and an aerosol  
26 conduit 22 internal diameter of 14 mm.  
27

28 In the preferred embodiment, the gas expansion chamber  
29 is circular in radial cross-section and elliptical  
30 in axial cross-section and is provided at the junction  
31 of the aerosol inlet port 18 with the aerosol torch  
32 conduit 22 by expanding the internal diameter of the  
33 aerosol conduit 22. Alternatively, the gas expansion  
34 chamber may have a different shape and/or  
35 configuration. It can also be located at other points  
36 where evaporation of the dopant ion solution occurs,

1 for example upstream along the aerosol inlet port 18 or  
2 downstream along the aerosol conduit 22.

3

4 The prevention of a blockage occurring as the dopant  
5 ions enter the aerosol conduit 22 is further assisted  
6 by reducing the angle of directionality  $\theta_2$  (the angle  
7 the aerosol inlet port makes with the torch axis (Y in  
8 Fig. 3)). In the preferred embodiment, significant  
9 reduction in the amount of condensation is provided by  
10  $\theta_2$  being substantially equal to  $10^\circ$ , which is in a  
11 preferred range of  $5^\circ$  to  $25^\circ$ . A reduction in the  
12 amount of condensation is also achieved if  $\theta_2$  is in the  
13 range of  $25^\circ$  to  $45^\circ$ .

14

15 The dimensions of the aerosol conduit 22 are selected  
16 to optimise the dopant process and to provide  
17 directionality to the flame whilst reducing the burner  
18 nozzle 26 temperature to below  $1300^\circ\text{C}$ . This prevents  
19 devitrification of the nozzle 26 which would otherwise  
20 provide unwanted contaminants.

21

22 In the preferred embodiment, with a deposition rate of  
23  $1 \mu\text{m}$  of base material per traversal of the FHD burner,  
24 it is possible to achieve doping levels of up to 0.72  
25 wt% for an  $\text{ErCl}_3$  solution strength of 1M with a carrier  
26 gas flow rate of  $2.4 \text{ litre min}^{-1}$ . Higher dopant levels  
27 can be achieved, for example, by maintaining the rare  
28 earth dopant conditions and reducing the halide flow  
29 rates or by increasing the concentration of the rare  
30 earth dopant solution.

31

32 Other dopant ions, for example, rare earth or heavy  
33 metal ions and combinations of ions can be incorporated  
34 using the burner 15 into the deposition stage.  
35 Suitable solutions including rare earth and/or heavy  
36 metal ions can be prepared at much higher

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1 concentrations than were hitherto known in the art  
2 without any accretion clogging the burner 15.

3

4 For example, a Nd doped planar silica ( $\text{SiO}_2 - \text{P}_2\text{O}_5$ )  
5 waveguide can be fabricated using the burner 15. An  
6 Nd/Al aqueous solution of 0.5M/0.4M can be used to  
7 provide the waveguide with dopant ion concentrations of  
8 0.25 wt% for Nd and 0.04 wt% for Al.

9

10 The modified FHD burner 15 therefore enables greater  
11 control of the ion doping process during the deposition  
12 stage of fabricating the waveguide. One or more ion  
13 species can be introduced during the deposition stage  
14 of fabricating the waveguide in a controlled manner to  
15 produce waveguides with more uniform and much higher  
16 dopant ion concentrations than known from the prior  
17 art.

18

19 While several embodiments of the present invention have  
20 been described and illustrated, it will be apparent to  
21 those skilled in the art once given this disclosure  
22 that various modifications, changes, improvements and  
23 variations may be made without departing from the  
24 spirit or scope of this invention.

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